Rev. F Dec.-2019

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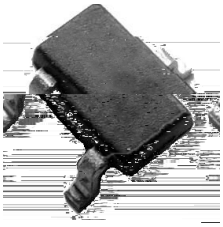
SOT23-3 N - CHANNEL MOSFET in a SOT23-3 Plastic Package.

V_{DS} (V) = 30V
I_D = 5.8 A (V_{GS} = 10V)
$R_{DS(ON)}$ < 32mΩ (V_{GS} = 1
$R_{DS(ON)}$ < 36mΩ (V_{GS} = 4
$R_{DS(ON)}$ < 56mΩ (V_{GS} = 2
无卤产品。HF Product.

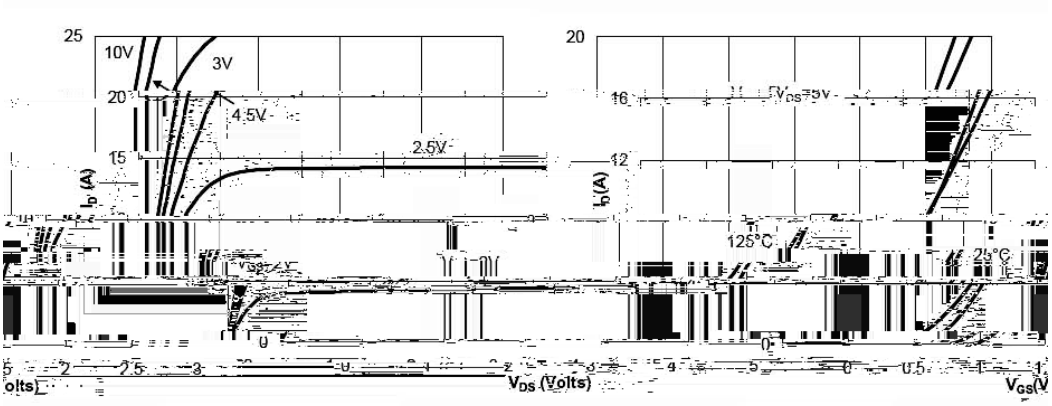
This device is suitable fo tch or in PWM applications.

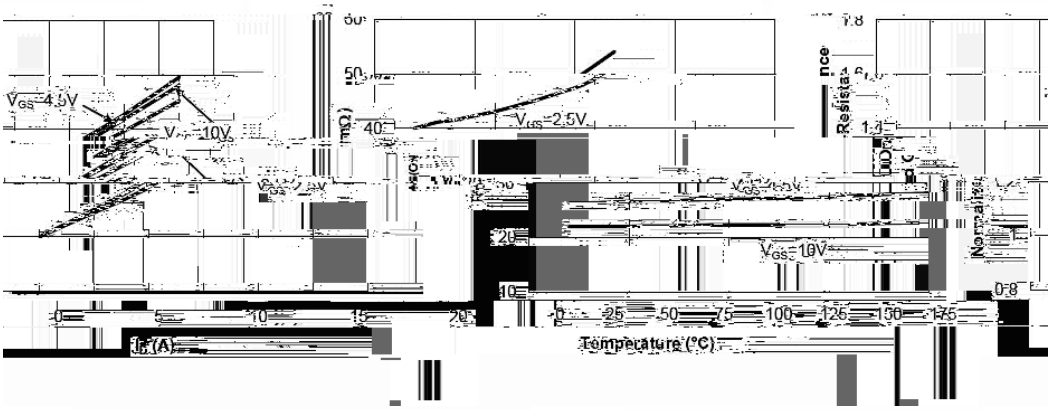


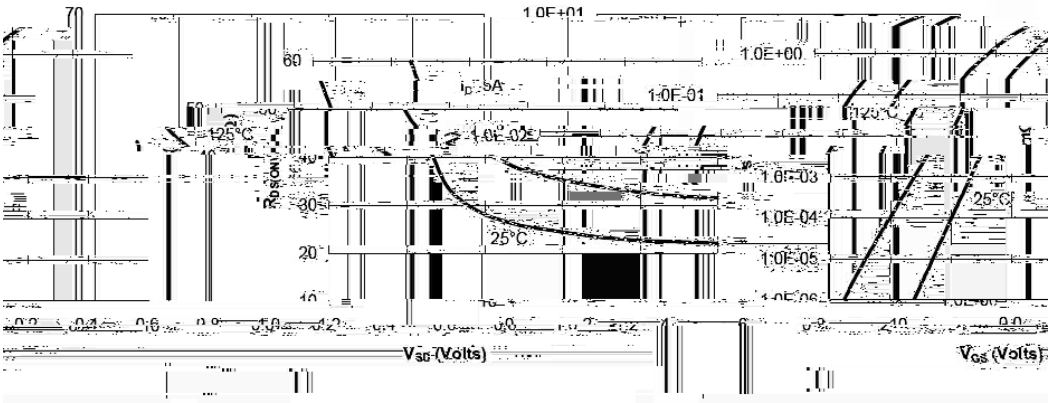
PIN1 G PIN 2 D

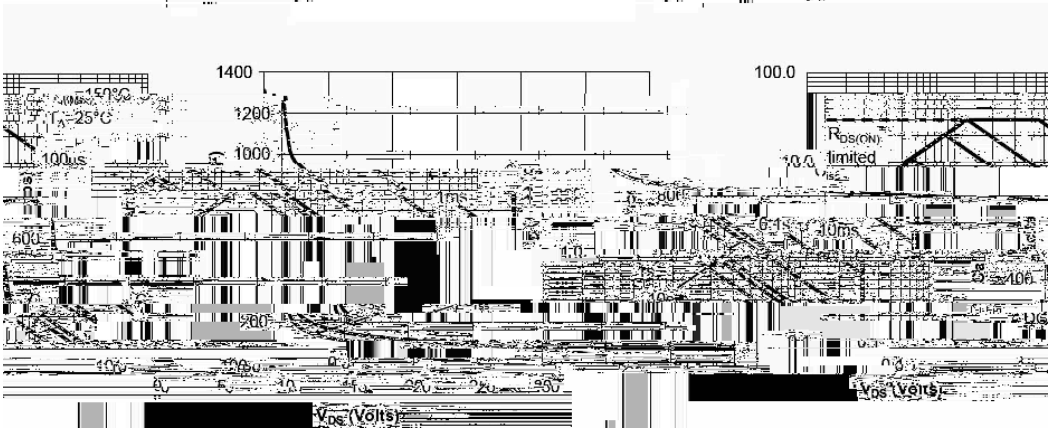
Marking	A0H

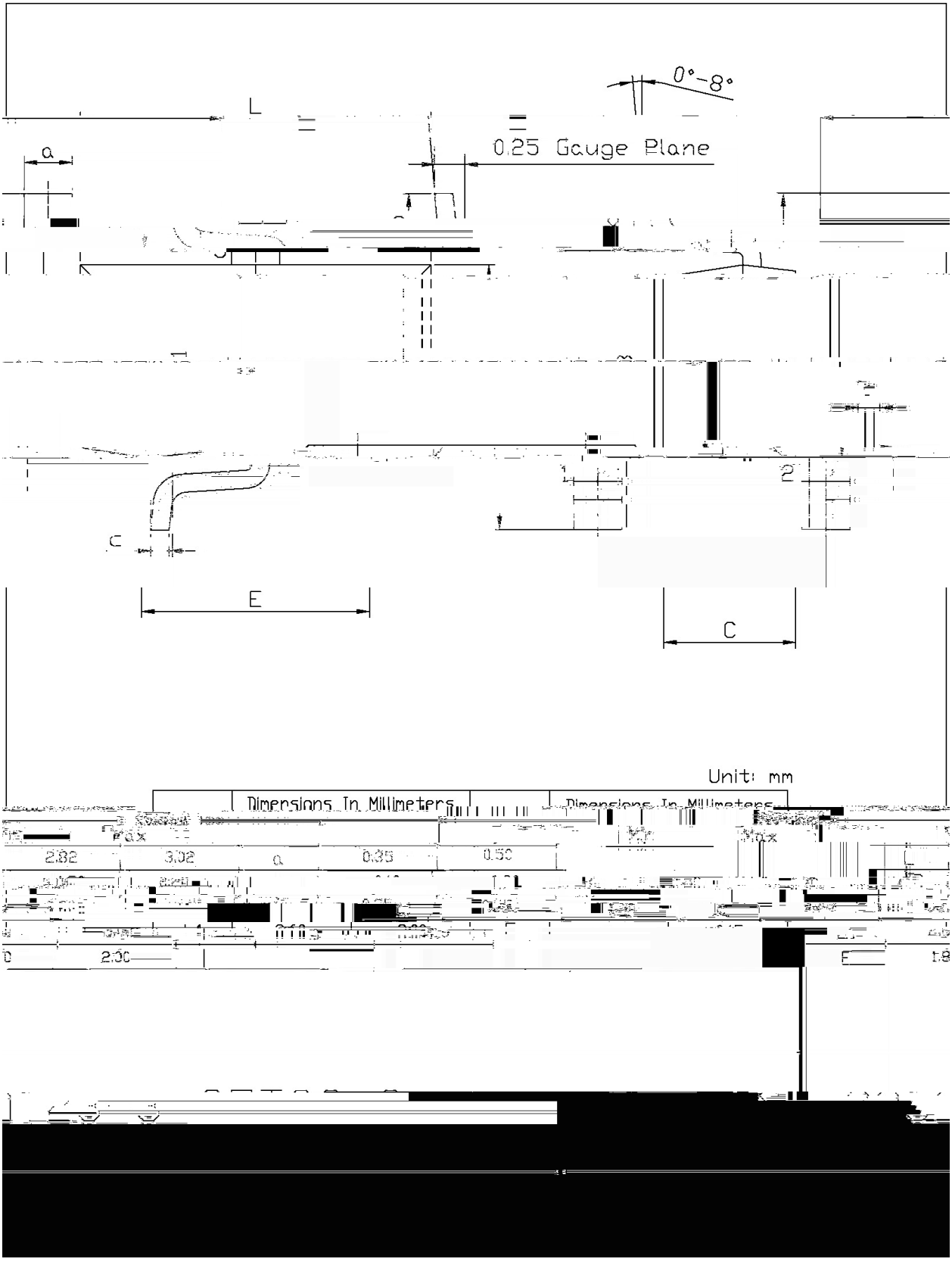
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Capacitance	C_{iss}	V_{DS}=15V V_{GS}=0V f=1MHz		823	1030	pF
Output Capacitance	C_{oss}			99		
Reverse Transfer Capacitance	C_{rss}			77		
Gate resistance	R_g	V_{GS}=0V V_{DS}=0V, f=1MHz		1.2	3.6	Ω
Total Gate Charge	Q_g	V_{GS}=4.5V, V_{DS}=15V, I_D=5.8A		9.7	12	nC
Gate Source Charge	Q_{gs}			1.6		
Gate Drain Charge	Q_{gd}			3.1		
Turn–On Delay Time	$t_{d(on)}$	V_{GS}=10V R_L=2.7Ω V_{DS}=15V R_{GEN}=3Ω		3.3	5	ns
Turn–On Rise Time	t_r			4.8	7	
Turn–Off Delay Time	$t_{d(off)}$			26.3	40	
Turn–Off Fall Time	t_f			4.1	6	
Body Diode Reverse Recovery Time	t_{rr}	I_F=5A dI/dt=100A/μs		16	20	ns
Body Diode Reverse Recovery Charge	Q_{rr}	I_F=5A dI/dt=100A/μs		8.9	12	nC

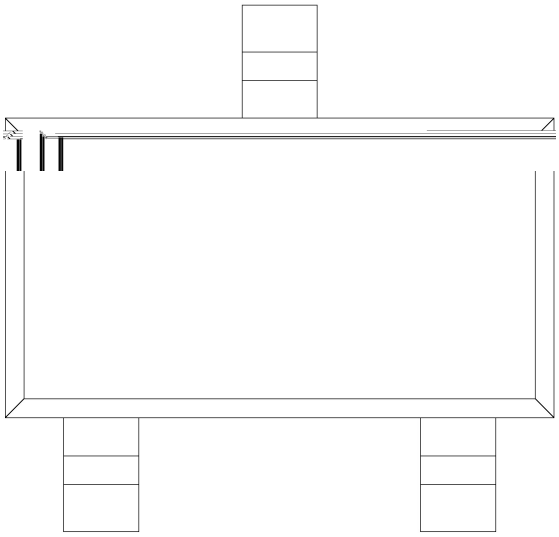

10V
3V
4.5V
2.5V
I_D (A)
V_{DS} (Volts)
V_{DS}=5V
125°C
25°C
V_{GS}(V


V_{GS}=4.5V
V_{GS}=2.5V
V_{GS}=10V
I_D (A)
Temperature (°C)
Normalized

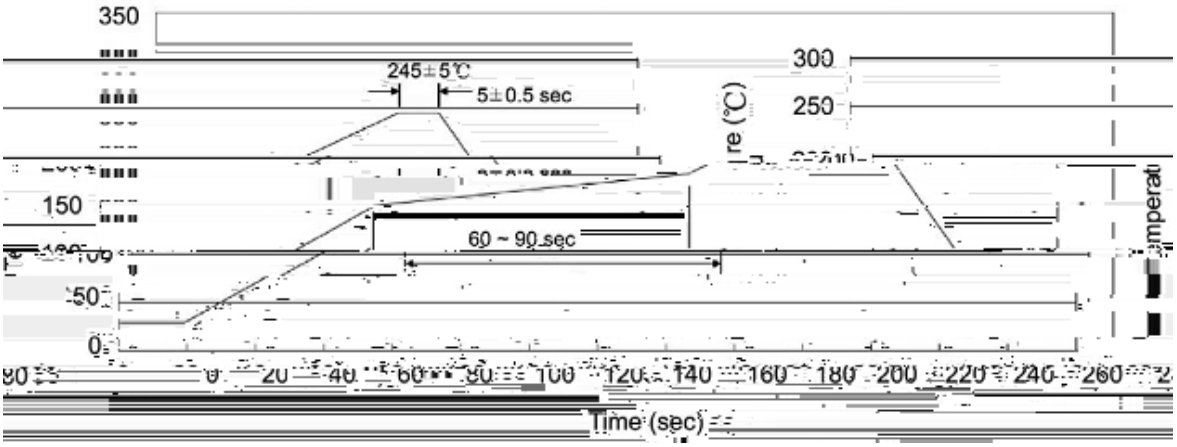

I_D=5A
125°C
25°C
V_{SD} (Volts)
V_{GS} (Volts)


25°C
100µs
1ms
10ms
100ms
1s
10s
DC
$R_{DS(ON)}$ limited
V_{DS} (Volts)


0°-8°
L
0.25 Gauge Plane
a
c
E
C
Unit: mm
Dimensions In Millimeters
Dimensions In Millimeters
2.82
3.02
0.35
0.50
2.30



Temperature Profile for IR Reflow Soldering(Pb-Free)



		Note:	
1	150 180 60 90sec;	1.Preheating:150~180 , Time:60~90sec.	
2	245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.	
3	2 10 /sec.	3. Cooling Speed: 2~10 /sec.	

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type	Units					Dimension		(unit mm^3)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
SOT-23-3	3,000	10	30,000	4	120,000	7″ ×8	210×205×205	445×230×435